

20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25°C
20V	21mΩ @ V _{GS} = 10V	17.0A
	27mΩ @ V _{GS} = 4.5V	15.0A
	40mΩ @ V _{GS} = 2.5V	12.3A

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- DC-DC Converters
- · Power management functions

Features and Benefits

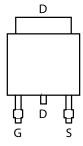
- · Low on-resistance
- · Fast switching speed
- · Low gate drive
- "Green" component and RoHS compliant (Note 1)

Mechanical Data

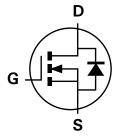
- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Marking Information: See BelowOrdering Information: See Below
- Weight: 0.33 grams (approximate)



TOP VIEW



PIN OUT -TOP VIEW



Equivalent Circuit

Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
DMN2027LK3-13	N2027L	13	16	2,500	

Note:

Marking Information



Oll = Manufacturer's Marking
N2027L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 09 = 2009)
WW = Week (01-52)

^{1.} Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.



Maximum Ratings @T_A = 25°C unless otherwise specified

Char	acteristic		Symbol Value		Unit	
Drain-Source voltage			V_{DSS}	20	V	
Gate-Source voltage			V_{GS}	±12	V	
		(Note 3)	I _D	17.0		
Continuous Drain current	$V_{GS} = 10V$	$T_A = 70^{\circ}C \text{ (Note 3)}$		13.6	Α	
		(Note 2)		11.6		
Pulsed Drain current V _{GS} = 10V ((Note 4)	I_{DM}	46.8	Α	
Continuous Source current (Body diode) (Note 3)			I _S	11.9	Α	
Pulsed Source current (Body diode) (Note 4)			I _{SM}	46.8	A	

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
	(Note 2)		4.18 33.44		
Power dissipation Linear derating factor	(Note 3)	P _D	8.9 71.4	W mW/°C	
	(Note 5)		2.14 17.1		
Thermal Resistance, Junction to Ambient	(Note 2) (Note 3) (Note 5)	R _θ JA	29.9 14.0 58.4	°C/W	
Thermal Resistance, Junction to Lead	(Note 6)	$R_{ hetaJL}$	2.46		
Operating and storage temperature range		T _J , T _{STG}	-55 to 150	°C	

Notes:

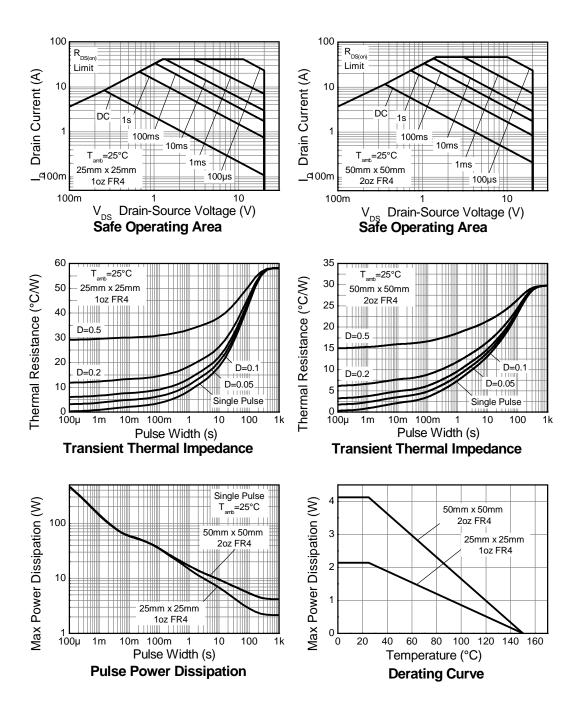
- 2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

- Same as note 2, except the device is measured at t ≤ 10 sec.
 Same as note 2, except the device is pulsed with D = 0.02 and pulse width 300 μs. The pulse current is limited by the maximum junction temperature.
 For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Thermal resistance from junction to solder-point (at the end of the drain lead).





Thermal Characteristics







Electrical Characteristics @TA = 25°C unless otherwise specified

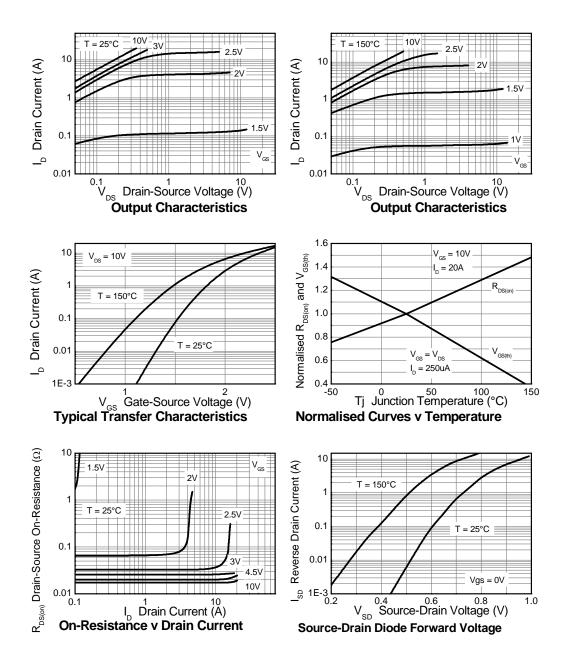
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$I_D = 250 \mu A, V_{GS} = 0V$		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	0.5	μА	V _{DS} = 20V, V _{GS} = 0	V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V _{GS} = ±12V, V _{DS} = 0	OV	
ON CHARACTERISTICS								
Gate Threshold Voltage	V _{GS(th)}	0.6	_	2.0	V	I_{D} = 250 μ A, V_{DS} = V	'GS	
				0.021		V _{GS} = 10V, I _D = 20A	1	
Static Drain-Source On-Resistance (Note 7)	R _{DS} (ON)	_	_	0.027	Ω	V _{GS} = 4.5V, I _D = 10A		
				0.040		V _{GS} = 2.5V, I _D = 4A		
Forward Transconductance (Notes 7 & 8)	g fs	_	31.7	_	S	V _{DS} = 15V, I _D = 10A		
Diode Forward Voltage (Note 7)	V _{SD}	_	0.89	1.0	V	I _S = 10A, V _G S= 0V		
Reverse recovery time (Note 8)	t _{rr}		121	_	ns	I _S = 10A, di/dt= 100A/μs		
Reverse recovery charge (Note 8)	Q _{rr}	_	583	_	nC			
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	C _{iss}	_	857	_	pF			
Output Capacitance	Coss	_	177	_	pF	V _{DS} = 10V, V _{GS} = 0' f= 1MHz	V	
Reverse Transfer Capacitance	C _{rss}	_	102	_	pF			
Total Gate Charge	Qg	_	5.2	_	nC	V _{GS} = 2.5V, I _D = 4A		
Total Gate Charge	Qg	_	9.1	_	nC		V _{DS} = 10V	
Gate-Source Charge	Q _{gs}	_	1.9	_	nC	V _{GS} = 4.5V I _D = 10A		
Gate-Drain Charge	Q_{gd}	_	3.2	_	nC			
Turn-On Delay Time (Note 9)	t _{D(on)}	_	5.4	_	ns			
Turn-On Rise Time (Note 9)	t _r	_	22.3	_	ns	V _{DD} = 10V, V _{GS} = 10V		
Turn-Off Delay Time (Note 9)	t _{D(off)}	_	18.7	_	ns	$I_D=10A, R_G \cong 6.0\Omega$		
Turn-Off Fall Time (Note 9)	t _f		12.6	—	ns	1		

Notes:

- Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%
 For design aid only, not subject to production testing.
 Switching characteristics are independent of operating junction temperatures.

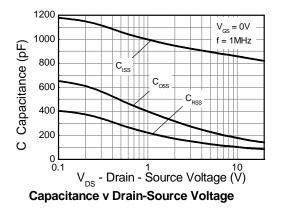


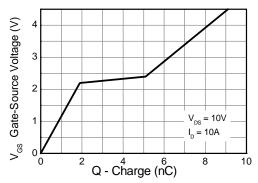
Typical Characteristics





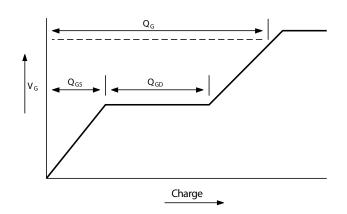
Typical Characteristics - continued





Gate-Source Voltage v Gate Charge

Test Circuits



Current regulator

12V 0.2µF 50k D.U.T

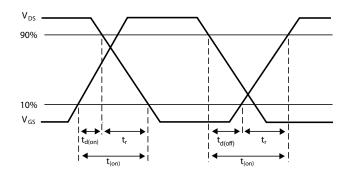
V_{DS}

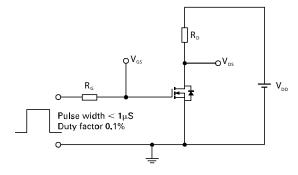
V_{SS}

D.U.T

Basic gate charge waveform

Gate charge test circuit



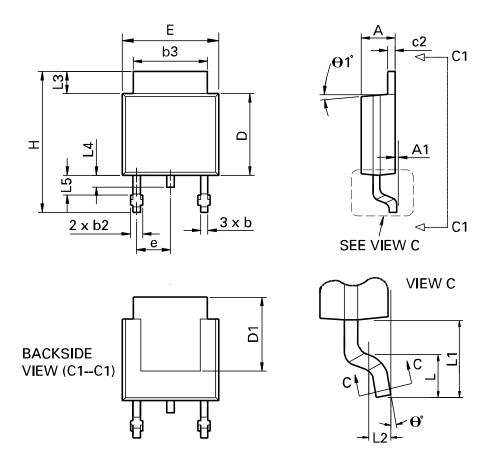


Switching time waveforms

Switching time test circuit

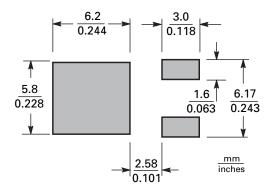


Package Outline Dimensions



DIM Inches		hes	Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	0.086	0.094	2.18	2.39	е	0.090 BSC		2.29 BSC	
A 1	-	0.005	-	0.127	Н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
С	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

Suggested Pad Layout



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